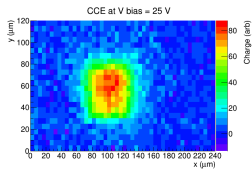
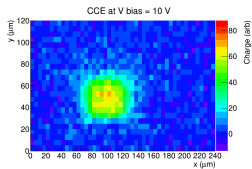
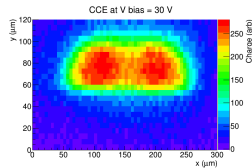
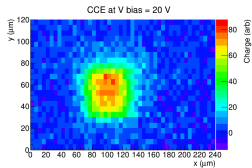
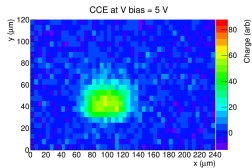
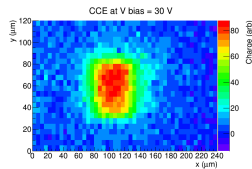
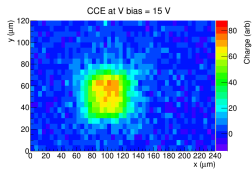
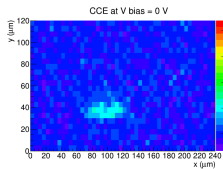


# Meritve na čipu HVCMOS RD50 W9 pri različnih stopnjah obsevanja

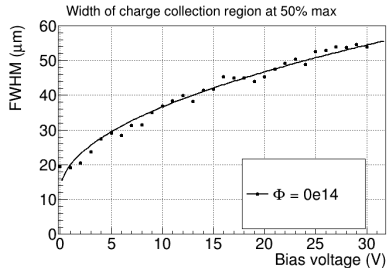
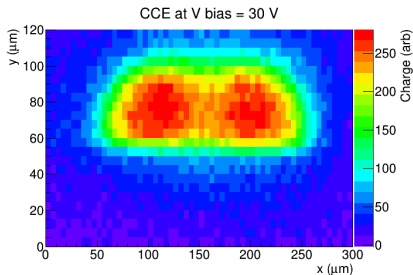
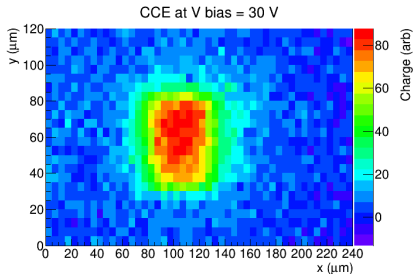
Petja Skomina

20. julij 2018

# bef irradi



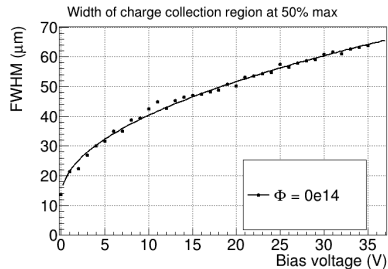
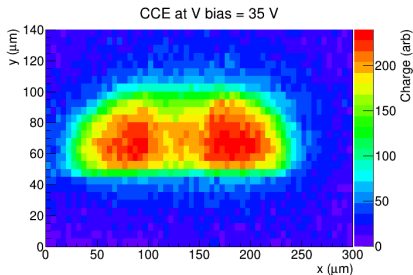
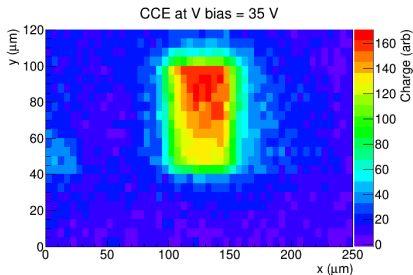
# bef irradi



► Širina pixla:  $50\mu\text{m}$

►  $N_{eff} = 0.2137$

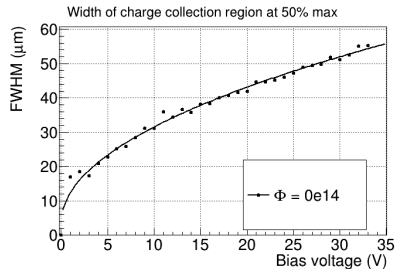
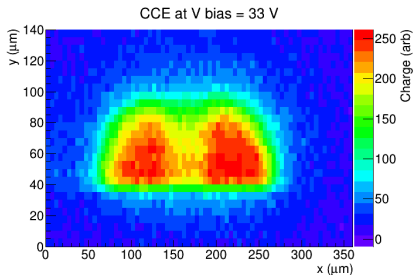
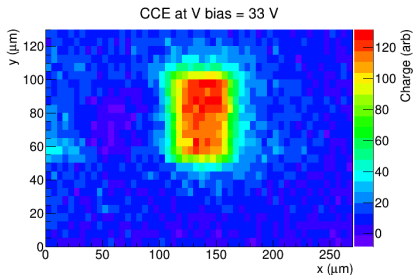
# irrad 2e13



► Širina pixla:  $50\mu\text{m}$

►  $N_{eff} = 0.1732$

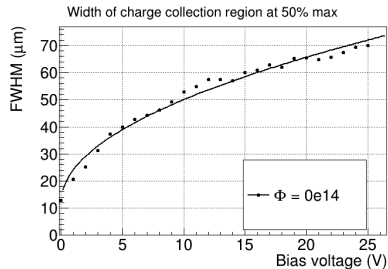
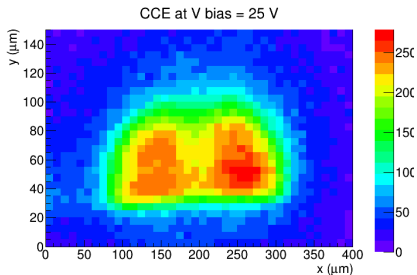
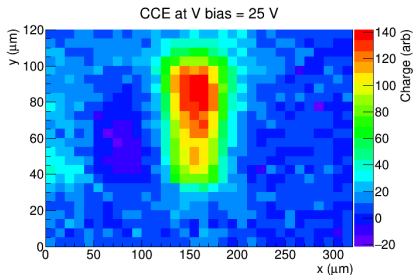
# irrad 5e13



► Širina pixla:  $50\mu\text{m}$

►  $N_{eff} = 0.1643$

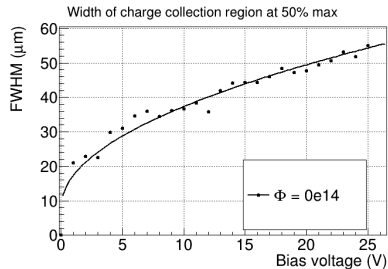
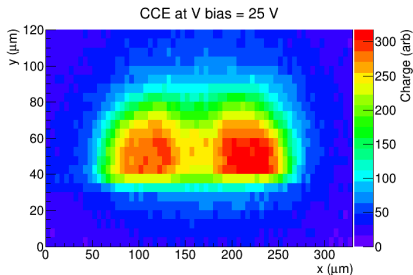
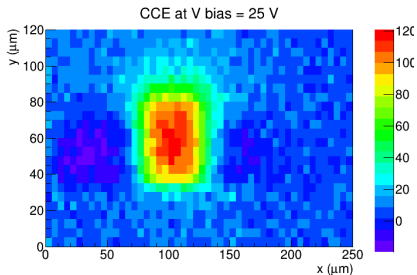
irrad 1e14



► Širina pixla:  $50\mu\text{m}$

►  $N_{eff} = 0.0908$

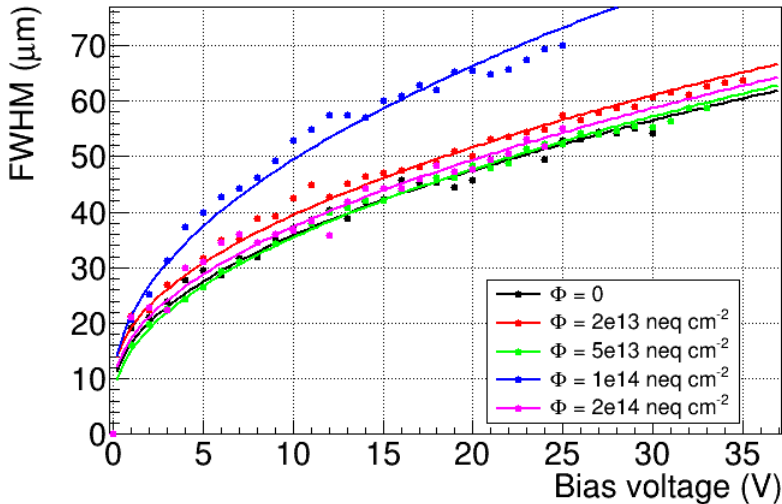
# irrad 2e14



► Širina pixla:  $50\mu\text{m}$

►  $N_{eff} = 0.1327$

Width of charge collection region at 50% max





# $N_{\text{eff}}$ vs. fluence

